Si3443BDV

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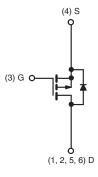
FEATURES

P-Channel 2.5 V (G-S) MOSFET

- TrenchFET[®] power MOSFET
- 100 % R_g tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



RoHS COMPLIANT HALOGEN



P-Channel MOSFET

Marking Code: 3B

PRODUCT SUMMARY					
V _{DS} (V)	-20				
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V	0.060				
$R_{DS(on)}$ max. (Ω) at V_{GS} = -2.7 V	0.090				
$R_{DS(on)}$ max. (Ω) at V_{GS} = -2.5 V	0.100				
Q _g typ. (nC)	6				
I _D (A) ^a	-4.7				
Configuration	Single				

ORDERING INFORMATION				
Package	TSOP-6			
Lead (Pb)-free	Si3443BDV-T1-E3			
Lead (Pb)-free and halogen-free	Si3443BDV-T1-GE3			

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage		V _{DS}	-20		
Gate-source voltage	V _{GS}	± 12	V		
Or attinuous durin comment (T 150 °O) a	T _A = 25 °C	- I _D	-3.6	٥	
Continuous drain current (T _J = 150 °C) ^a	T _A = 70 °C		-2.8		
Pulsed drain current		I _{DM}	-20	А	
Continuous source current (diode conduction) ^a	۱ _S	-0.9			
Maximum power dissipation ^a	T _A = 25 °C	Р	1.1	W	
Maximum power dissipation ~	T _A = 70 °C	P _D	0.7	vv	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	t ≤ 5 s	R _{thJA}	50	62.5	°C/W
	Steady state		90	110	
Maximum junction-to-foot (drain)	Steady state	R _{thJF}	30	36	

Note

a. Surface mounted on FR4 board, $t \leq 5 \mbox{ s}$



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \ \mu A$	-0.6	-	-1.4	V	
Gate-body leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 12 V$	-	-	± 100	nA	
Zero gate voltage drain current	I	$V_{DS} = -20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	-	-	-1	- uA	
Zero gate voltage drain current	I _{DSS}	V_{DS} = -20 V, V_{GS} = 0 V, T_{J} = 70 °C	-	-	-5		
On-state drain current ^a	I _{D(on)}	$V_{DS} = -5 V, V_{GS} = -4.5 V$	-15	-	-	А	
		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -4.7 \text{ A}$	-	0.048	0.060	Ω	
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -2.7 \text{ V}, I_D = -3.8 \text{ A}$	-	0.070	0.090		
		$V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -1 \text{ A}$	-	0.080	0.100		
Forward transconductance ^a	g _{fs}	$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -4.7 \text{ A}$	-	11	-	S	
Diode forward voltage ^a	V _{SD}	$I_{\rm S}$ = -1.7 A, $V_{\rm GS}$ = 0 V	-	-0.8	-1.2	V	
Dynamic ^b							
Total gate charge	Qg		-	6	9		
Gate-source charge	Q _{gs}	V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_{D} = - 4.7 A	-	1.4	-	nC	
Gate-drain charge	Q _{gd}		-	1.9	-		
Gate resistance	R _g	f = 1 MHz	5	9.5	16.2	Ω	
Turn-on delay time	t _{d(on)}		-	22	35		
Rise time	t _r	V_{DD} = - 10 V, R_L = 10 Ω	-	35	55		
Turn-off delay time	t _{d(off)}	$I_D\cong$ - 1.0 A, V_{GEN} = - 4.5 V, R_g = 6 Ω	-	45	70	ns	
Fall time	t _f		-	25	40		
Source-drain reverse recovery time	t _{rr}	I _F = - 1.7 A, dl/dt = 100 A/μs	-	25	50		

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

b. Guaranteed by design, not subject to production testing

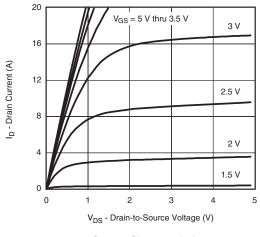
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



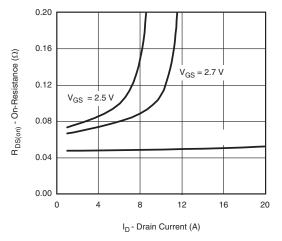
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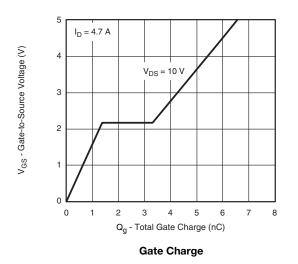
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

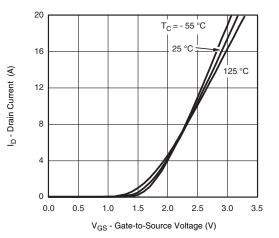


Output Characteristics

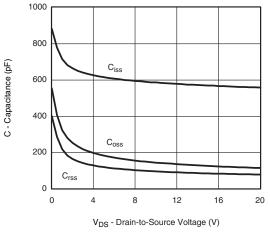


On-Resistance vs. Drain Current

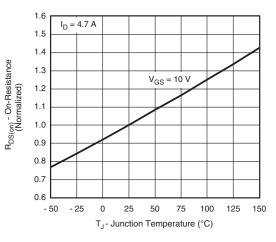




Transfer Characteristics



Capacitance



On-Resistance vs. Junction Temperature

S-09.0660-Rev. C, 20-Apr-09

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Document Number: 72749

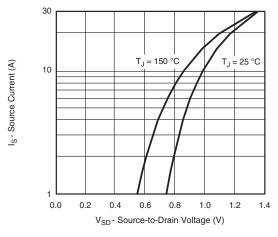
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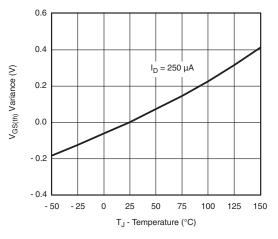
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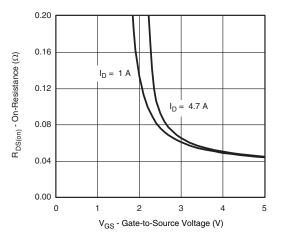
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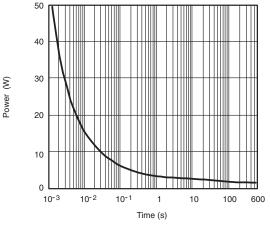
Source-Drain Diode Forward Voltage



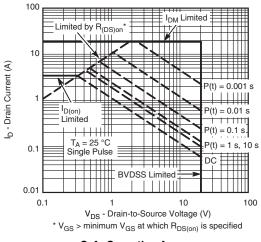




On-Resistance vs. Gate-to-Source Voltage







Safe Operating Area

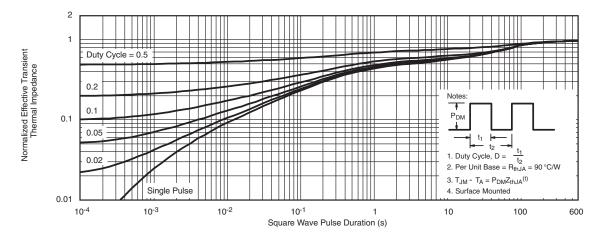
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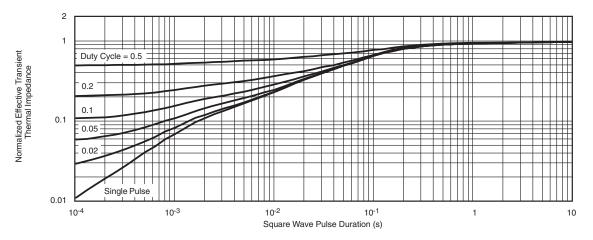


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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72749.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



	MIL	LIMETER	RS	INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	-	1.10	0.036	-	0.043
A ₁	0.01	-	0.10	0.0004	-	0.004
A ₂	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
Е	2.70	2.85	2.98	0.106	0.112	0.117
E ₁	1.55	1.65	1.70	0.061	0.065	0.067
е	0.95 BSC			0.0374 BSC		
e ₁	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L ₁		0.60 Ref			0.024 Ref	
L ₂	0.25 BSC				0.010 BSC	
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom				7° Nom	
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

PAD Pattern



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Recommended Land Pattern For TSOP-5L / TSOP-6L





TSOP 5L





Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	



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